# 2SC4606

# Silicon NPN epitaxial planar type

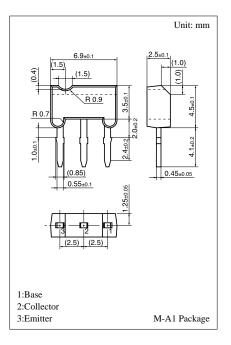
For low-frequency driver amplification Complementary to 2SA1762

### Features

- High collector to emitter voltage V<sub>CEO</sub>.
- Optimum for the driver stage of a low-frequency and 25 to 30W output amplifier.
- M type package allowing easy automatic and manual insertion as well as stand-alone fixing to the printed circuit board.

Parameter	Symbol	Ratings	Unit
Collector to base voltage	V <sub>CBO</sub>	80	V
Collector to emitter voltage	V <sub>CEO</sub>	80	V
Emitter to base voltage	V <sub>EBO</sub>	5	V
Peak collector current	I <sub>CP</sub>	1	А
Collector current	I <sub>C</sub>	0.5	А
Collector power dissipation	$P_{C}^{*}$	1	W
Junction temperature	Tj	150	°C
Storage temperature	T <sub>stg</sub>	-55 ~ +150	°C

#### Absolute Maximum Ratings (Ta=25°C)



\* Printed circuit board: Copper foil area of 1cm<sup>2</sup> or more, and the board thickness of 1.7mm for the collector portion

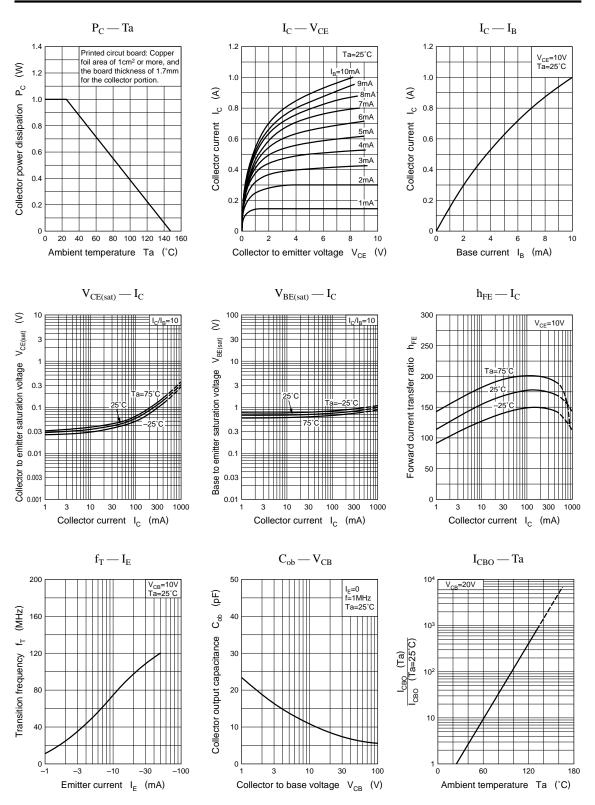
#### Electrical Characteristics (Ta=25°C)

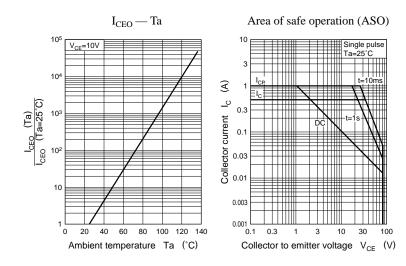
Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	I <sub>CBO</sub>	$V_{CB} = 20V, I_E = 0$			0.1	μA
Collector to base voltage	V <sub>CBO</sub>	$I_{\rm C} = 10 \mu A, I_{\rm E} = 0$	80			V
Collector to emitter voltage	V <sub>CEO</sub>	$I_{\rm C} = 100 \mu A, I_{\rm B} = 0$	80			v
Emitter to base voltage	V <sub>EBO</sub>	$I_{\rm E} = 10 \mu A, I_{\rm C} = 0$	5			v
	h <sub>FE1</sub> *1	$V_{CE} = 10V, I_{C} = 150mA^{*2}$	130		330	
Forward current transfer ratio	h <sub>FE2</sub>	$V_{CE} = 5V, I_C = 500mA^{*2}$	50	100		
Collector to emitter saturation voltage	V <sub>CE(sat)</sub>	$I_{\rm C} = 300 {\rm mA}, I_{\rm B} = 30 {\rm mA}^{*2}$		0.2	0.4	v
Base to emitter saturation voltage	V <sub>BE(sat)</sub>	$I_{\rm C} = 300 {\rm mA}, I_{\rm B} = 30 {\rm mA}^{*2}$		0.85	1.2	v
Transition frequency	f <sub>T</sub>	$V_{CB} = 10V, I_E = -50mA, f = 200MHz$		120		MHz
Collector output capacitance	C <sub>ob</sub>	$V_{CB} = 10V, I_E = 0, f = 1MHz$		11	20	pF

\*1hFE1 Rank classification

Rank	R	S
h <sub>FE1</sub>	130 ~ 220	185 ~ 330

\*2 Pulse measurement





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